

**IN THE CLAIMS:**

Please amend the claims as follows:

1. (Previously presented) A transmission line comprising:

a signal strip;

a resistive layer opposed to the signal strip with a dielectric layer disposed

between the resistive layer and the signal strip; and

a ground conductor electrically connected to the resistive layer,

wherein,

a high frequency current is induced in the resistive layer through capacitance formed by the dielectric layer between the signal strip and the resistive layer when a high frequency signal of a predetermined frequency is transmitted through the signal strip, and when resistance per unit length generated when the high frequency current flows in the resistive layer, and between the resistive layer and the ground conductor, is defined as an additional resistance, and resistance per unit length generated when the high frequency current flows through the ground conductor is defined as a ground resistance, the additional resistance is larger than the ground resistance,

wherein a width of the resistive layer is larger than a width of the signal strip,

the resistive layer is formed such that the whole width thereof is opposed to the signal strip,

the signal strip is formed on a top face of the dielectric layer,

the resistive layer is formed between a substrate and the dielectric layer,

the ground conductor is formed on a bottom face of the substrate, and

the resistive layer is connected to the ground conductor via a penetrating conductor penetrating the substrate.

2. (Previously presented) The transmission line according to claim 1, wherein a length of the resistive layer is $1/16$ or more of an effective wavelength λ of a signal of an upper limit frequency of the high frequency signal.

3. (Previously presented) The transmission line according to claim 1, wherein conductivity of a material constituting the resistive layer is smaller than conductivity of the ground conductor.

4. (Previously presented) The transmission line according to claim 1, wherein the conductivity of the material constituting the resistive layer is in the range of 1×10^3 S/m or more and 1×10^7 S/m or less.

5. (Previously presented) The transmission line according to claim 4, wherein the conductivity of the material constituting the resistive layer is in the range of 1×10^3 S/m or more and 1×10^5 S/m or less.

6. (Previously presented) The transmission line according to claim 1, wherein the resistive layer is formed from at least one material selected from the group consisting of chrome, nickel chrome alloy, iron-chrome alloy, thallium, a chrome-silicon oxide composite, titanium, an impurity doped semiconductor, and polycrystalline or amorphous semiconductors formed by polysilicon or the like.

7-9. (Cancelled)

10. (Previously presented) The transmission line according to claim 1, wherein the penetrating conductor is formed on an edge of the resistive layer.

11. (Previously presented) The transmission line according to claim 1, wherein a plurality of the penetrating conductors are formed along a longitudinal direction of the resistive layer with a spacing.

12-13. (Cancelled)

14. (Previously presented) A semiconductor integrated circuit device comprising:

a main signal circuit on which at least one active element is disposed; and

a bias supplying circuit having a transmission line and supplying bias to the main signal circuit through the transmission line,

wherein at least a part of the transmission line is the transmission line according to claim 1.

15. (Currently amended) The semiconductor integrated circuit according to claim 14, wherein

the transmission line has a first transmission line connected to the main signal circuit and a second transmission line connected to the first transmission line;

the first transmission line is formed by a coplanar waveguide or a microstrip;

the second transmission line is formed by the at least a part of the transmission line; and

an end of the first transmission line closer to the main signal circuit is connected to a ground terminal through a bypass condenser.

16. (Previously presented) The semiconductor integrated circuit according to claim 14, wherein

the semiconductor integrated circuit device is a single-stage high frequency amplifier having an amplifying transistor as the at least one active element; and

the bypass supplying circuit is at least one of an input side circuit that is of a front stage side with respect to the active element of the main signal circuit and an output circuit that is of a rear stage side with respect to the active element of the main signal circuit.

17. (Previously presented) The semiconductor integrated circuit according to claim 16, wherein

the semiconductor integrated circuit device is a multi-stage high frequency amplifier having a plurality of amplifying transistors as the at least one active element; and

the bypass supplying circuit is at least one of an input side circuit that is of a front stage side with respect to the active element of the main signal circuit, an output circuit that is of a rear stage side with respect to the active element of the main signal circuit, and an interstage circuit that is disposed between the plurality of amplifying transistors.